

L Number	Hits	Search Text	DB	Time stamp
2	66	(peripheral adj portion) and 257/\$.ccls. and (nonvolatile adj memory)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/05/17 12:45
3	0	5659191.pn. and (gate adj length)	USPÄT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/05/17 08:07
4	0	5659191.pn. and (gate adj width)	USPÄT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/05/17 08:08
5	0	5659191.pn. and (gate adj size)	USPÄT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/05/17 08:08
6	2	5659191.pn. and (gate)	USPÄT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/05/17 08:12
7	1	5659191.pn. and (length or width)	USPÄT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/05/17 09:51
8	11	(peripheral adj portion) and (gate adj length) and (nonvolatile adj memory)	USPÄT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/05/17 11:54
9	203	oxidized adj insulating adj (film or layer or region)	USPÄT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/05/17 09:08
10	95	(oxidized adj insulating adj (film or layer or region)) and (257/\$.ccls. or 438/4.ccls.)	USPÄT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/05/17 09:26
11	3	(oxidized adj insulating adj (film or layer or region)) and (257/\$.ccls. or 438/4.ccls.) and (nonvolatile adj memory)	USPÄT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/05/17 09:09
12	159	((prevent adj (oxidizing or oxidation)) same (insulating adj (film or layer or region))) and (257/\$.ccls. or 438/4.ccls.)	USPÄT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/05/17 09:27
13	2	5479054.pn. and (prevent)	USPÄT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/05/17 10:38
14	0	5479054.pn. and (oxidized)	USPÄT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/05/17 10:18
15	1	5479054.pn. and (oxidation)	USPÄT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/05/17 10:03

16	0	5479054.pn. and (nonvolatile)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/05/17 10:18
17	0	5479054.pn. and (non adj volatile)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/05/17 10:18
18	0	5479054.pn. and (memory)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/05/17 10:19
19	0	5479054.pn. and dram	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/05/17 10:19
20	0	5479054.pn. and sram	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/05/17 10:19
21	0	5479054.pn. and ram	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/05/17 10:20
22	0	5479054.pn. and prom	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/05/17 10:54
23	1	5747370.pn. and (oxidized or oxidation)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/05/17 10:53
24	0	5747370.pn. and (sin or (silicon adj nitride))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/05/17 10:54
25	1	5479054.pn. and (sin or (silicon adj nitride))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/05/17 10:54
26	59	((metal or (metal adj silicide)) adj gate) and (nonvolatile adj memory)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/05/17 11:56
27	17	((metal or (metal adj silicide)) adj gate) and (nonvolatile adj memory) and tungsten	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/05/17 11:56
28	785	(peripheral adj circuit adj region) and 257/\$.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/05/17 12:47
29	256	(contact adj hole adj diameter) and 257/\$.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/05/17 12:48

30	76	(peripheral adj circuit adj region) and (nonvolatile adj memory) and 257/\$.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/05/17 12:47
31	7	(contact adj hole adj diameter) and (nonvolatile adj memory) and 257/\$.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/05/17 12:48